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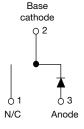
Ultralow V_F Hyperfast Rectifier for Discontinuous Mode PFC, 8 A FRED Pt[®]

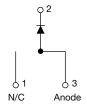




TO-263AB (D²PAK)

TO-262AA





VS-8ETL06SPbF

VS-8ETL06-1PbF

PRODUCT SUMMARY	PRODUCT SUMMARY						
Package	TO-263AB (D ² PAK), TO-262AA						
I _{F(AV)}	8 A						
V_{R}	600 V						
V _F at I _F	0.81 V						
t _{rr} typ.	60 ns						
T _J max.	175 °C						
Diode variation	Single die						

FEATURES

• Benchmark ultralow forward voltage drop



- Hyperfast recovery time
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- ROHS COMPLIANT HALOGEN FREE

- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

State of the art, ultralow V_F, soft-switching hyperfast rectifiers optimized for discontinuous (critical) mode (DCM) power factor correction (PFC).

The minimized conduction loss, optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

The device is also intended for use as a freewheeling diode in power supplies and other power switching applications.

APPLICATIONS

AC/DC SMPS 70 W to 400 W

e.g. laptop and printer AC adaptors, desktop PC, TV and monitor, games units and DVD AC/DC power supplies.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage	V_{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 160 °C	8				
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	175	Α			
Peak repetitive forward current	I _{FM}		16				
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	600	-	-			
Forward voltage	V _F	I _F = 8 A	-	0.96	1.05	V		
		I _F = 8 A, T _J = 150 °C	-	0.81	0.86			
Deverse legicore everent		V _R = V _R rated	-	0.05	5			
Reverse leakage current I _R	IR	T _J = 150 °C, V _R = V _R rated	-	20	100	μΑ		
Junction capacitance	C _T	V _R = 600 V	-	17	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

Revision: 15-Nov-16 1 Document Number: 94029



VS-8ETL06SPbF, VS-8ETL06-1PbF

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1 A, dI_F/dt = 1$	00 A/μs, V _R = 30 V	-	60	100	
Povorno ropovoni timo		$I_F = 8 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	150	250	
Reverse recovery time	t _{rr}	T _J = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	170	-	ns
		T _J = 125 °C		-	250	-	
Dools recovery ourset	,	T _J = 25 °C		-	15	-	Α
Peak recovery current	I _{RRM}	T _J = 125 °C		-	20	-	^
Reverse recovery charge	0	T _J = 25 °C		-	1.3	-	
	Q _{rr}	T _J = 125 °C		-	2.6	-	μC

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.4	2	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Mojaht			-	2.0	-	g
Weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking davisa		Case style TO-263AB (D2PAK)		8ETL06S		
Marking device		Case style TO-262		8ETL06-1		

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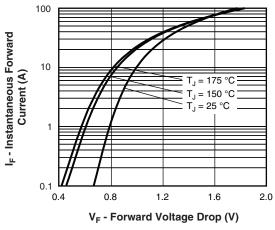


Fig. 1 - Typical Forward Voltage Drop Characteristics

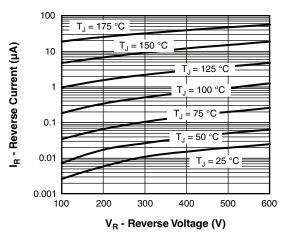


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

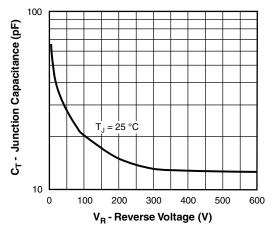


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

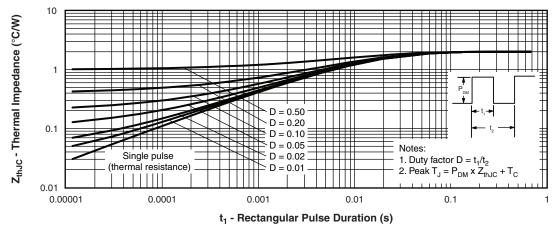


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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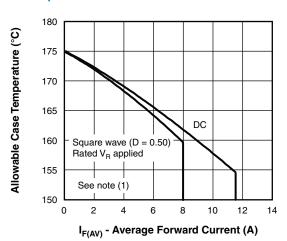


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

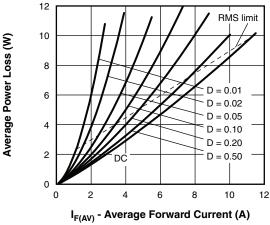


Fig. 6 - Forward Power Loss Characteristics

5000 $I_{\rm F} = 16 \, {\rm A}$ 4500 $I_F = 8 A$ 4000 3500 Q_{rr} (nC) 3000 2500 2000 1500 $V_{R} = 390 \text{ V}$ 1000 T_J = 125 °C $T_1 = 25 \,^{\circ}\text{C}$ 500 100 1000 dl_E/dt (A/µs)

Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

(1) Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 6); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

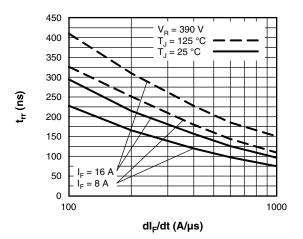


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

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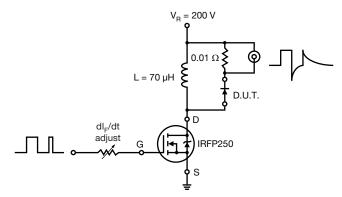
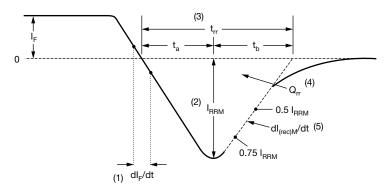


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

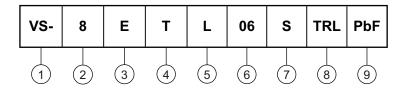
Fig. 10 - Reverse Recovery Waveform and Definitions

VS-8ETL06SPbF, VS-8ETL06-1PbF

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ORDERING INFORMATION TABLE





1 - Vishay Semiconductors product

Current rating (8 A)

3 - E = single diode

4 - T = TO-220, D²PAK

L = ultralow V_F hyperfast recovery

6 - Voltage rating (06 = 600 V)

• -1 = TO-262

None = tube (50 pieces)

• TRL = tape and reel (left oriented, for D2PAK package)

• TRR = tape and reel (right oriented, for D²PAK package)

9 - PbF = lead (Pb)-free

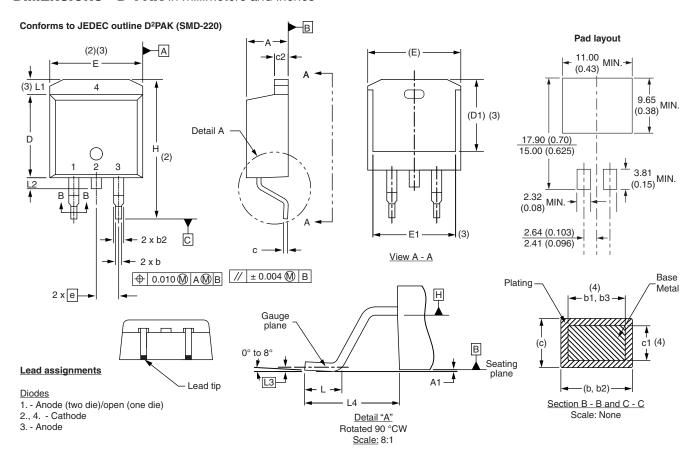
LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95014					
Part marking information	www.vishay.com/doc?95008					
Packaging information	www.vishay.com/doc?95032					
SPICE model	www.vishay.com/doc?96055					



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D²PAK, TO-262

DIMENSIONS - D²PAK in millimeters and inches



SYMBOL	MILLIN	IETERS	INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIN	IETERS	INCHES		NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54	BSC	0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25 BSC		0.010	BSC		
L4	4.78	5.28	0.188	0.208		

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}\,$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch

(7) Outline conforms to JEDEC outline TO-263AB

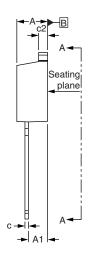
Document Number: 95014 Revision: 31-Mar-09

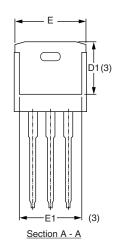
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D²PAK, TO-262



DIMENSIONS - TO-262 in millimeters and inches





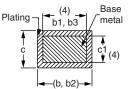
⊕ 0.010**⋒**|A**⋒**|B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

CYMPOL	MILLIM	ETERS	INC	INCHES		
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	2.03	3.02	0.080	0.119		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
С	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	
D1	6.86	8.00	0.270	0.315	3	
Е	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100) BSC		
L	13.46	14.10	0.530	0.555		
L1	-	1.65	-	0.065	3	
L2	3.56	3.71	0.140	0.146		

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

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